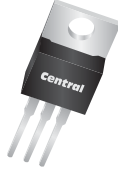


CDM22010-650

**SILICON
N-CHANNEL POWER MOSFET
10 AMP, 650 VOLT**



TO-220 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CDM22010-650 is a high current, 650 Volt N-Channel power MOSFET designed for high voltage, fast switching applications such as Power Factor Correction (PFC), lighting and power inverters. This MOSFET combines high voltage capability with low $r_{DS(ON)}$, low threshold voltage and low gate charge.

MARKING CODE: CDM10-650

APPLICATIONS:

- Power Factor Correction
- Motor drives
- Alternative energy inverters
- Solid state lighting

FEATURES:

- High voltage capability ($V_{DS}=650V$)
- Low gate charge ($Q_{GS}=8.0nC$)
- Low $r_{DS(ON)}$ (0.88Ω)

MAXIMUM RATINGS: ($T_A=25^\circ C$ unless otherwise noted)

	SYMBOL		UNITS
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	30	V
Continuous Drain Current (Steady State)	I_D	10	A
Maximum Pulsed Drain Current, $t_p=10\mu s$	I_{DM}	40	A
Continuous Source Current (Body Diode)	I_S	10	A
Maximum Pulsed Source Current (Body Diode)	I_{SM}	40	A
Single Pulse Avalanche Energy (Note 1)	E_{AS}	608	mJ
Power Dissipation	P_D	2.0	W
Power Dissipation ($T_C=25^\circ C$)	P_D	156	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-55 to +150	$^\circ C$
Thermal Resistance	θ_{JC}	0.8	$^\circ C/W$
Thermal Resistance	θ_{JA}	62.5	$^\circ C/W$

Note 1: $L=30mH$, $I_{AS}=6.2A$, $V_{DD}=50V$, $R_G=25\Omega$, Initial $T_J=25^\circ C$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ C$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{GSSF}, I_{GSSR}	$V_{GS}=30V, V_{DS}=0$		10	100	nA
I_{DSS}	$V_{DS}=650V, V_{GS}=0$		0.03	1.0	μA
BV_{DSS}	$V_{GS}=0, I_D=250\mu A$	650			V
$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2.0	2.8	4.0	V
V_{SD}	$V_{GS}=0, I_S=10A$		0.9	1.4	V
$r_{DS(ON)}$	$V_{GS}=10V, I_D=5.0A$		0.88	1.0	Ω
C_{rss}	$V_{DS}=25V, V_{GS}=0, f=1.0MHz$		1.2		pF
C_{iss}	$V_{DS}=25V, V_{GS}=0, f=1.0MHz$		1168		pF
C_{oss}	$V_{DS}=25V, V_{GS}=0, f=1.0MHz$		129		pF

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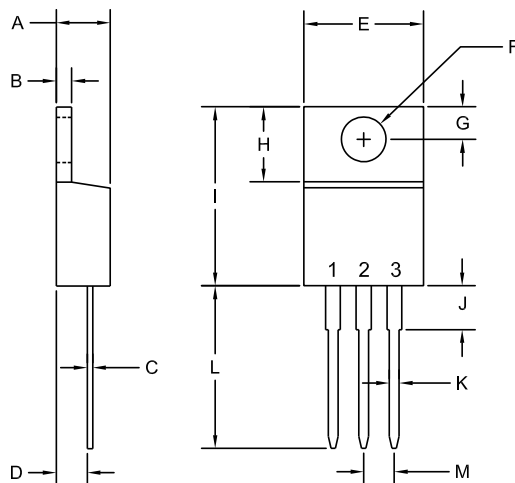


ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	TYP	UNITS
$Q_{g(\text{tot})}$	$V_{DS}=520\text{V}$, $V_{GS}=10\text{V}$, $I_D=10\text{A}$ (Note 2)	20	nC
Q_{gs}	$V_{DS}=520\text{V}$, $V_{GS}=10\text{V}$, $I_D=10\text{A}$ (Note 2)	8.0	nC
Q_{gd}	$V_{DS}=520\text{V}$, $V_{GS}=10\text{V}$, $I_D=10\text{A}$ (Note 2)	7.0	nC
t_d	$V_{DD}=325\text{V}$, $I_D=10\text{A}$, $R_G=25\Omega$ (Note 2)	20	ns
t_r	$V_{DD}=325\text{V}$, $I_D=10\text{A}$, $R_G=25\Omega$ (Note 2)	33	ns
t_s	$V_{DD}=325\text{V}$, $I_D=10\text{A}$, $R_G=25\Omega$ (Note 2)	57	ns
t_f	$V_{DD}=325\text{V}$, $I_D=10\text{A}$, $R_G=25\Omega$ (Note 2)	36	ns
t_{rr}	$V_{GS}=0$, $I_S=10\text{A}$, $di/dt=100\text{A}/\mu\text{s}$ (Note 2)	570	ns
Q_{rr}	$V_{GS}=0$, $I_S=10\text{A}$, $di/dt=100\text{A}/\mu\text{s}$ (Note 2)	4.7	μC

Note 2: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

TO-220 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.170	0.190	4.31	4.82
B	0.045	0.055	1.15	1.39
C	0.013	0.026	0.33	0.65
D	0.083	0.107	2.10	2.72
E	0.394	0.417	10.01	10.60
F (DIA)	0.140	0.157	3.55	4.00
G	0.100	0.118	2.54	3.00
H	0.230	0.270	5.85	6.85
I	0.560	0.625	14.23	15.87
J	-	0.250	-	6.35
K	0.025	0.038	0.64	0.96
L	0.500	0.579	12.70	14.70
M	0.090	0.110	2.29	2.79

TO-220 (REV: R2)

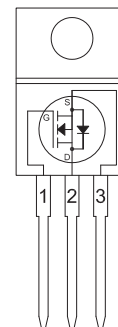
R2

LEAD CODE:

- 1) Gate
- 2) Drain
- 3) Source
- Tab) Drain

MARKING CODE: CDM10-650

PIN CONFIGURATION



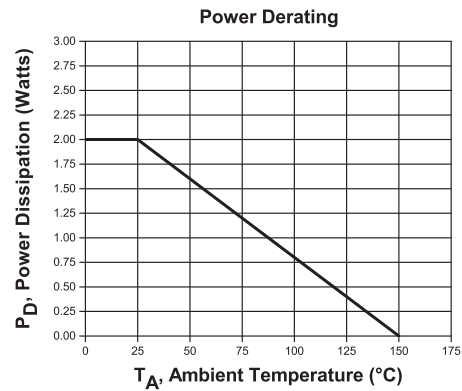
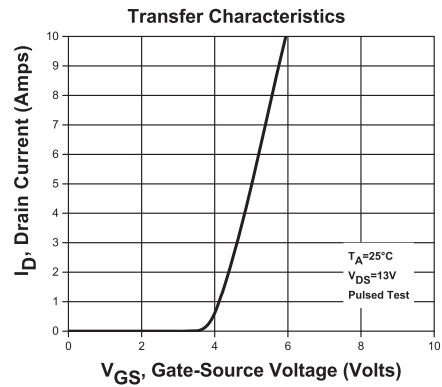
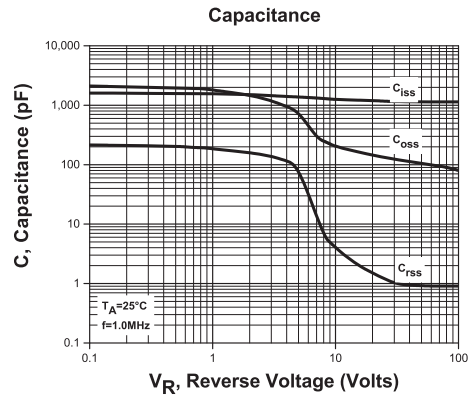
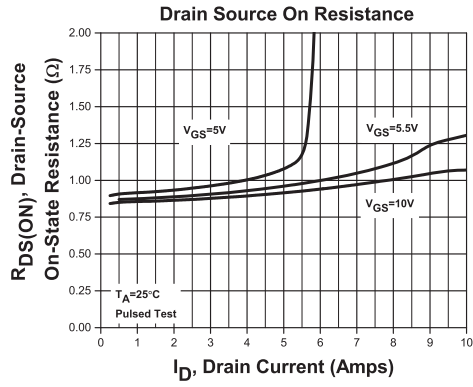
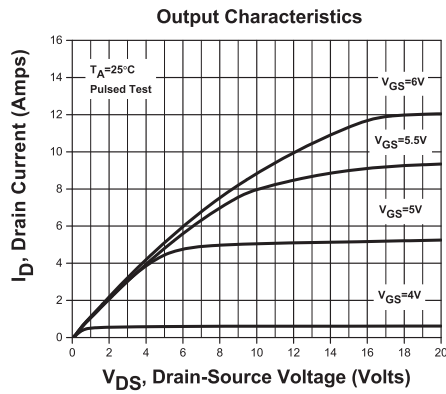
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TYPICAL ELECTRICAL CHARACTERISTICS



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